

## N - CHANNEL ENHANCEMENT MODE FAST POWER MOS TRANSISTOR

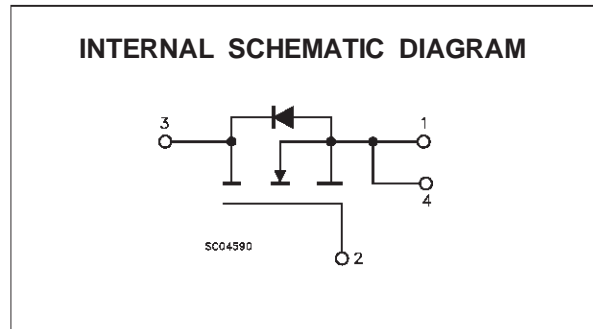
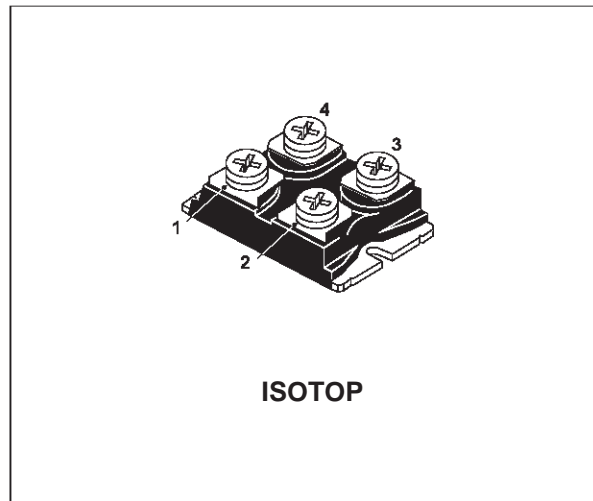
PRELIMINARY DATA

TYPE	V <sub>DSS</sub>	R <sub>DS(on)</sub>	I <sub>D</sub>
STE40NA60	600 V	< 0.135 Ω	40 A

- TYPICAL R<sub>DS(on)</sub> = 0.12 Ω
- HIGH CURRENT POWER MODULE
- AVALANCHE RUGGED TECHNOLOGY
- VERY LARGE SOA - LARGE PEAK POWER CAPABILITY
- EASY TO MOUNT
- SAME CURRENT CAPABILITY FOR THE TWO SOURCE TERMINALS
- EXTREMELY LOW R<sub>th</sub> (Junction to case)
- VERY LOW INTERNAL PARASITIC INDUCTANCE
- ISOLATED PACKAGE UL RECOGNIZED

### APPLICATIONS

- SMPS & UPS
- MOTOR CONTROL
- WELDING EQUIPMENT
- OUTPUT STAGE FOR PWM, ULTRASONIC CIRCUITS



### ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V <sub>DS</sub>	Drain-source Voltage (V <sub>GS</sub> = 0)	600	V
V <sub>DGR</sub>	Drain- gate Voltage (R <sub>GS</sub> = 20 kΩ)	600	V
V <sub>GS</sub>	Gate-source Voltage	± 30	V
I <sub>D</sub>	Drain Current (continuous) at T <sub>c</sub> = 25 °C	40	A
I <sub>D</sub>	Drain Current (continuous) at T <sub>c</sub> = 100 °C	26	A
I <sub>DM</sub> (●)	Drain Current (pulsed)	160	A
P <sub>tot</sub>	Total Dissipation at T <sub>c</sub> = 25 °C	460	W
	Derating Factor	3.6	W/°C
T <sub>stg</sub>	Storage Temperature	-55 to 150	°C
T <sub>j</sub>	Max. Operating Junction Temperature	150	°C
V <sub>ISO</sub>	Insulation Withstand Voltage (AC-RMS)	2500	V

(●) Pulse width limited by safe operating area

# STE40NA60

## THERMAL DATA

$R_{thj-case}$	Thermal Resistance Junction-case	Max	0.27	$^{\circ}C/W$
$R_{thc-h}$	Thermal Resistance Case- heatsink With Conductive Grease Applied	Max	0.05	$^{\circ}C/W$

## AVALANCHE CHARACTERISTICS

Symbol	Parameter	Max Value	Unit
$I_{AR}$	Avalanche Current, Repetitive or Not-Repetitive (pulse width limited by $T_j$ max, $\delta < 1\%$ )	20	A
$E_{AS}$	Single Pulse Avalanche Energy (starting $T_j = 25^{\circ}C$ , $I_D = I_{AR}$ , $V_{DD} = 50 V$ )	3000	mJ

## ELECTRICAL CHARACTERISTICS ( $T_{case} = 25^{\circ}C$ unless otherwise specified)

OFF

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$V_{(BR)DSS}$	Drain-source Breakdown Voltage	$I_D = 500 \mu A$ $V_{GS} = 0$	900			V
$I_{DSS}$	Zero Gate Voltage Drain Current ( $V_{GS} = 0$ )	$V_{DS} = \text{Max Rating}$ $V_{DS} = 0.8 \times \text{Max Rating}$ $T_c = 125^{\circ}C$			250 1000	$\mu A$ $\mu A$
$I_{GSS}$	Gate-body Leakage Current ( $V_{DS} = 0$ )	$V_{GS} = \pm 30 V$			$\pm 200$	nA

ON (\*)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS} = V_{GS}$ $I_D = 1 mA$	2.25	3	3.75	V
$R_{DS(on)}$	Static Drain-source On Resistance	$V_{GS} = 10V$ $I_D = 20 A$		0.12	0.135	$\Omega$
$I_{D(on)}$	On State Drain Current	$V_{DS} > I_{D(on)} \times R_{DS(on)max}$ $V_{GS} = 10 V$	40			A

## DYNAMIC

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$g_{fs} (*)$	Forward Transconductance	$V_{DS} > I_{D(on)} \times R_{DS(on)max}$ $I_D = 20 A$	20			S
$C_{iss}$	Input Capacitance	$V_{DS} = 25 V$ $f = 1.0 MHz$ $V_{GS} = 0$		13000	16000	pF
$C_{oss}$	Output Capacitance			1500	1700	pF
$C_{rss}$	Reverse Transfer Capacitance			350	450	pF

**ELECTRICAL CHARACTERISTICS** (continued)

## SWITCHING ON

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$	Turn-on Time	$V_{DD} = 300\text{ V}$ $I_D = 20\text{ A}$		55	75	ns
$t_r$	Rise Time	$R_G = 4.7\ \Omega$ $V_{GS} = 10\text{ V}$		95	125	ns
$Q_g$	Total Gate Charge	$V_{DD} = 480\text{ V}$ $I_D = 40\text{ A}$ $V_{GS} = 10\text{ V}$		460	600	nC
$Q_{gs}$	Gate-Source Charge			48		nC
$Q_{gd}$	Gate-Drain Charge			217		nC

## SWITCHING OFF

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$t_{r(Voff)}$	Off-voltage Rise Time	$V_{DD} = 480\text{ V}$ $I_D = 40\text{ A}$		95	125	ns
$t_f$	Fall Time	$R_G = 4.7\ \Omega$ $V_{GS} = 10\text{ V}$		30	40	ns
$t_c$	Cross-over Time			140	180	ns

## SOURCE DRAIN DIODE

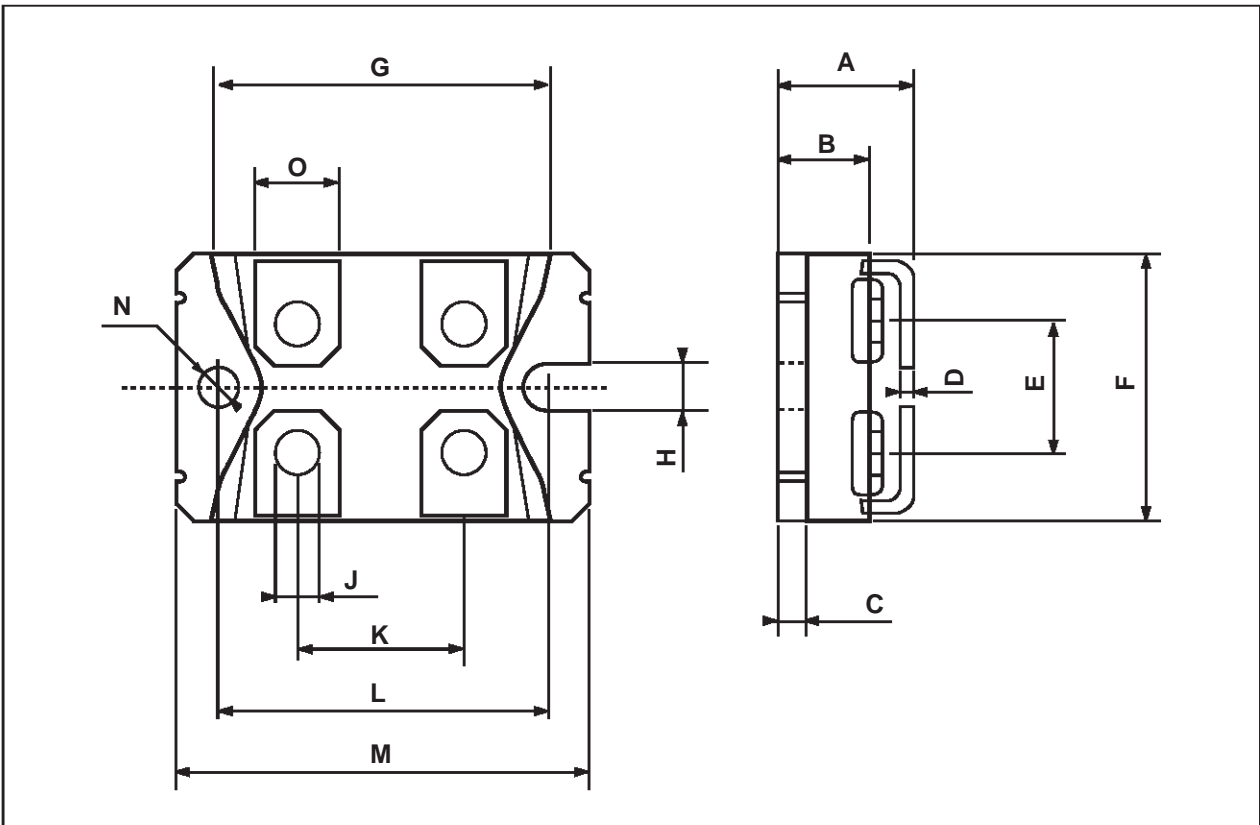
Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$I_{SD}$	Source-drain Current				40	A
$I_{SDM}(\bullet)$	Source-drain Current (pulsed)				160	A
$V_{SD} (*)$	Forward On Voltage	$I_{SD} = 40\text{ A}$ $V_{GS} = 0$			1.6	V
$t_{rr}$	Reverse Recovery Time	$I_{SD} = 40\text{ A}$ $di/dt = 100\text{ A}/\mu\text{s}$ $V_R = 100\text{ V}$ $T_j = 150\text{ }^\circ\text{C}$		1050		ns
$Q_{rr}$	Reverse Recovery Charge			31.5		$\mu\text{C}$
$I_{RRM}$	Reverse Recovery Current			60		A

(\*) Pulsed: Pulse duration = 300  $\mu\text{s}$ , duty cycle 1.5 %

(\bullet) Pulse width limited by safe operating area

**ISOTOP MECHANICAL DATA**

DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A	11.8		12.2	0.466		0.480
B	8.9		9.1	0.350		0.358
C	1.95		2.05	0.076		0.080
D	0.75		0.85	0.029		0.033
E	12.6		12.8	0.496		0.503
F	25.15		25.5	0.990		1.003
G	31.5		31.7	1.240		1.248
H	4			0.157		
J	4.1		4.3	0.161		0.169
K	14.9		15.1	0.586		0.594
L	30.1		30.3	1.185		1.193
M	37.8		38.2	1.488		1.503
N	4			0.157		
O	7.8		8.2	0.307		0.322



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